

Small Signal Switching Diodes

REVERSE VOLTAGE : 80 V
RECTIFIED CURRENT: 130 mA

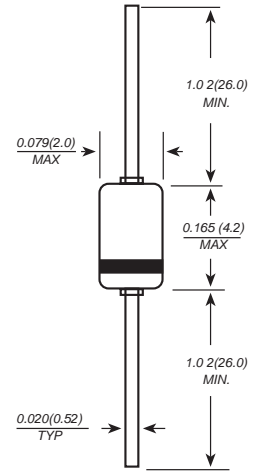
Features

- Lead Free Finish/Rohs Compliant (Note1) ("P")Suffix designates Compliant ,See ordering information)
- High speed.(trr=1.2ns typ)
- High Reliability
- silicon epitaxial planar

MECHANICAL DATA

- Case: DO-35, glass case
- Polarity: Color band denotes cathode

DO-35(GLASS)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameters	Symbol	Value	Unit
Reverse Voltage	V_R	80	V
Peak Reverse Voltage	V_{RM}	90	V
Power Dissipation	P_d	300	mW
Operating junction temperature	T_j	-55to+150	°C
Storage temperature range	T_s	-55to+150	°C
Working Inverse Voltage	W_{IV}	75	V
Average Rectified Current	I_o	130	mA
Peak Forward Current	I_{FM}	400	mA

@ $t < 1s$ and $T_j = 25^\circ C$

Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Electrical Specification ($T_A = 25^\circ C$ unless otherwise specified)

Symbols	Parameter	Test Condition	Limits		Unit
			Min	Max	
I_R	Reverse Leakage Current	$V_R = 80V$	---	0.5	μA
V_F	Forward Voltage	$I_F = 100mA$	---	1.2	V
T_{RR}	Reverse Recovery Time	$I_F = 10mA, I_R = 1.0mA$ $R_L = 50\Omega$ $I_{RR} = 1mA$	---	4	nS
C_r	Capacitance between terminals	$V_R = 0.5V_{dc}, f = 1.0MHz$	---	2.0	pF

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

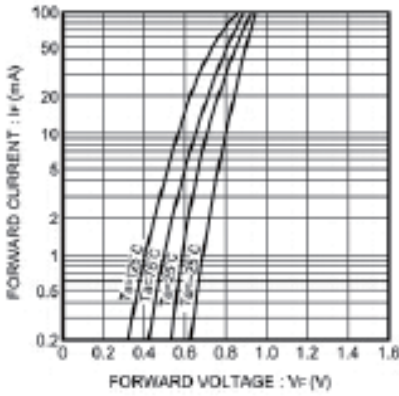


Fig. 1 Forward characteristics

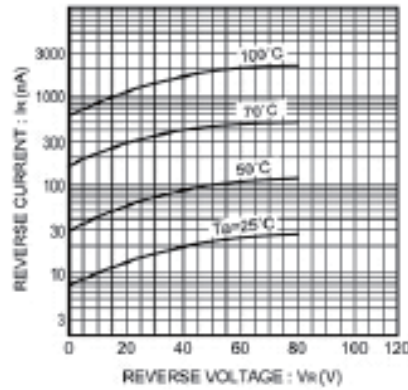


Fig. 2 Reverse characteristics

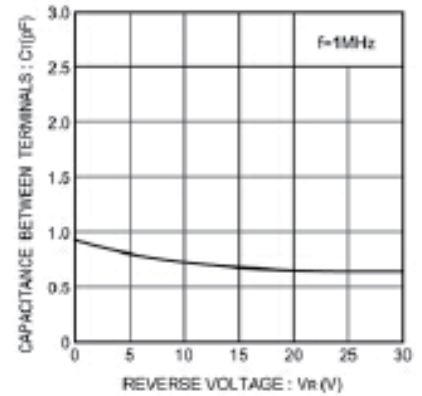


Fig. 3 Capacitance between terminals characteristics

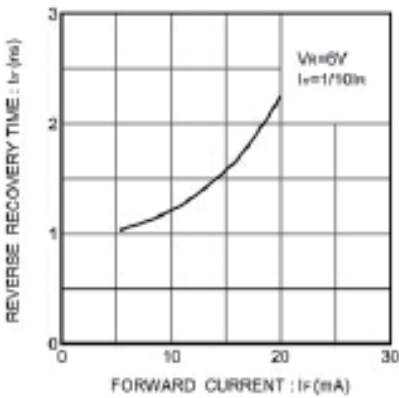


Fig. 4 Reverse recovery time characteristics

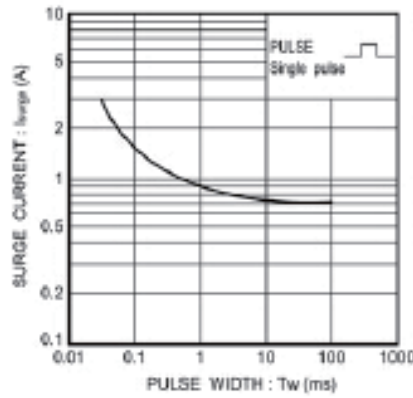


Fig. 5 Surge current characteristics

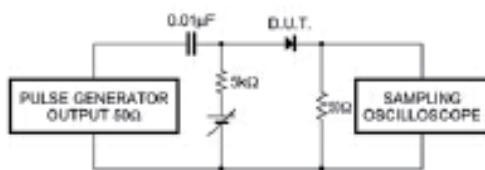


Fig. 6 Reverse recovery time (t_r) measurement circuit